REMARKS

The application has been carefully reviewed in light of the Office Action dated May 2, 2003. Claims 1 to 52 are in the application, of which Claims 1, 12, 26, 27, 38 and 52 are the independent claims. Reconsideration and further examination are respectfully requested.

Claims 12 to 25 and 38 to 51 were withdrawn from consideration pursuant to a telephonic restriction requirement. In this regard, Applicants wish to confirm their telephonic election to prosecute the Group I claims (Claims 1 to 11, 26 to 37 and 52). The restriction requirement is, however, traversed.

The restriction requirement is traversed is on the ground that there would not be undue burden in examining the two groups of claims in a single application. In particular, MPEP § 808 makes clear that in order to require restriction between independent or distinct inventions, reasons for insisting upon a restriction requirement, such as undue burden, must also be shown. In the present instance, it is not believed that there would be undue burden in examining Groups I and II in a single application, since the two groups of claims are not so different as would require a burden on the Examiner that is significantly beyond that of the normal burdens of examination. Accordingly, reconsideration and withdrawal of the restriction requirement are respectfully requested.

Claims 3 and 29 were rejected under 35 U.S.C. §112, second paragraph. Applicants have carefully reviewed and amended these claims to attend to the issues raised in the Office Action. Accordingly, withdrawal of the Section 112 rejection is respectfully requested.

Claims 27 to 29, 33 to 35 and 52 were rejected under 35 U.S.C. §102(b) over U.S. Patent No. 4,243,472 (O'Neill). Claims 36 and 37 were rejected under 35 U.S.C. §103(a) over O'Neill. Claim 31 was rejected under 35 U.S.C. §103(a) over O'Neill and further in view of Japanese Patent No. 11-199376 (Ukiyo). Claim 32 was rejected under 35 U.S.C. §103(a) over O'Neill and further in view of U.S. Patent No. 4,293,371 (Kokta). Claims 1 to 3, 7 to 11 and 26 were rejected under 35 U.S.C. §103(a) over O'Neill in view of U.S. Patent No. 5,603,762 (Kokune) or Applicants' allegedly admitted prior art. Claim 5 was rejected under 35 U.S.C. §103(a) over O'Neill in view of Kokune or Applicants' allegedly admitted prior art and further in view of Ukiyo. Claim 6 was rejected under 35 U.S.C. §103(a) over O'Neill in view of Kokune or Applicants' allegedly admitted prior art and further in view of U.S. Patent No. 5,902,394 (Burkhart). Reconsideration and withdrawal of the rejections are respectfully requested.

The present invention as recited by amended Claims 1 and 26 concerns a liquid phase growth process or a substrate production method which includes the steps of: immersing a substrate in a melt held in a crucible, a crystal material having been dissolved in the melt; and growing a crystal on the substrate. The process or method also has the step of rotating the crucible independently from the substrate, where the substrate is disposed at a position set aside from the center of rotation of the crucible. The crystal is grown on the surface of the substrate thus disposed. No part of the substrate is disposed at the center of rotation of the crucible.

The present invention as recited by amended Claims 27 and 52 concerns a liquid phase growth process or substrate member production method which includes the steps of: immersing a substrate in a melt held in a crucible, the substrate being supported with a

supporting rack, and a crystal material having been dissolved in the melt; and growing a crystal on the substrate. The process or method also has the step of rotating the supporting rack, where the substrate is disposed at a position set aside from the center of rotation of the supporting rack, and the crystal is grown on the surface of the substrate thus disposed. No part of the substrate is disposed at the center of rotation of the supporting rack.

Thus, according to one feature of the invention as recited by the claims under consideration, no part of the substrate is disposed at the center of rotation of the crucible or at the center of rotation of the supporting rack. By virtue of this feature, uniform growth on the substrate is more easily achieved. This is due to the fact that the melt flows more slowly at the center of the crucible or supporting rack. See, for example, page 9, lines 5 to 14, of the specification.

O'Neill is not seen to teach or suggest at least the foregoing feature.

As shown in Figs. 1 to 4 of O'Neill, a portion of each of the wafers (12) is disposed at the center of rotation of the crucible (14).

This can be contrasted to the embodiment shown in Fig. 1 of the present invention, in which no part of the substrate groups (102) is disposed at the center of rotation of the crucible (105), and to the embodiment shown in Fig. 12 of the present invention, in which no part of the substrate groups (1202) is disposed at the center of rotation of the supporting rack (1200).

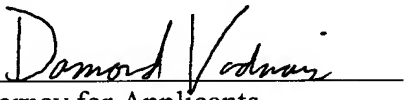
Ukiyo, Kokta, Kokune, Applicants' allegedly admitted prior art and Burkhart are not seen to remedy the foregoing deficiencies of O'Neill. Applicants therefore conclude that the applied references do not teach or suggest the claimed invention, either singly or in

the combinations proposed by the Office Action, and it is respectfully requested that the Section 102 and Section 103 rejections be withdrawn.

No other matters being raised, the entire application is believed to be in condition for allowance, and such action is courteously solicited.

Applicants' undersigned attorney may be reached in our Washington, D.C. office by telephone at (202) 530-1010. All correspondence should continue to be directed to our below-listed address.

Respectfully submitted,



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